

2SD2375

Silicon NPN triple diffusion planar type

For power amplification with high forward current transfer ratio

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

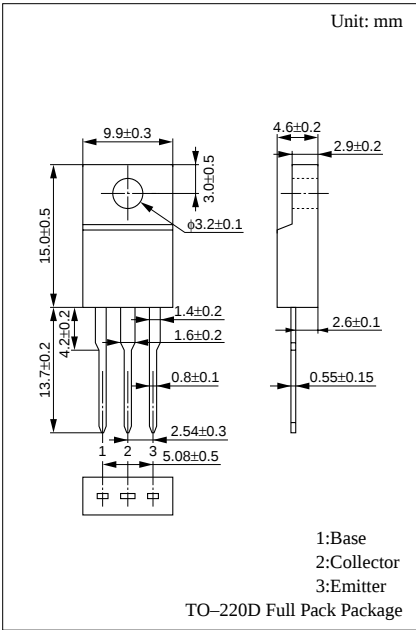
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	80	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	6	A
Collector current	I_C	3	A
Base current	I_B	1	A
Collector power dissipation	P_C	25	W
		2	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

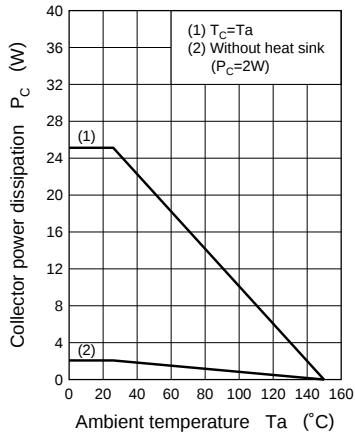
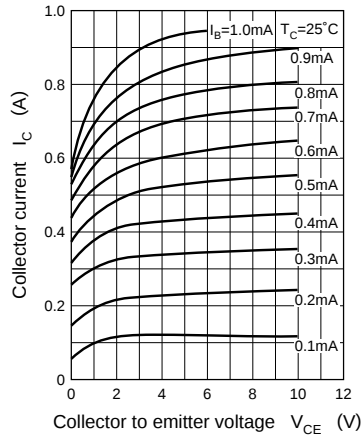
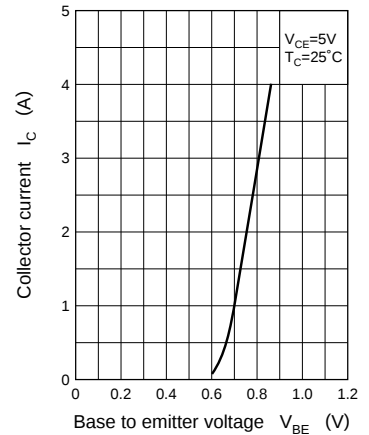
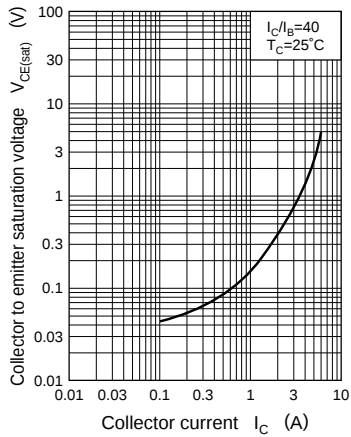
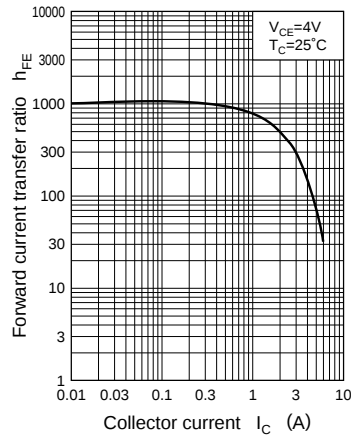
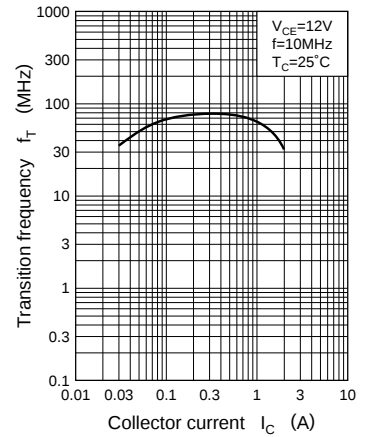
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 80\text{V}, I_E = 0$			100	μA
	I_{CEO}	$V_{CE} = 40\text{V}, I_B = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 25\text{mA}, I_B = 0$	60			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 4\text{V}, I_C = 0.5\text{A}$	500		1500	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 0.05\text{A}$			1	V
Transition frequency	f_T	$V_{CE} = 12\text{V}, I_C = 0.2\text{A}, f = 10\text{MHz}$		50		MHz

* h_{FE} Rank classification

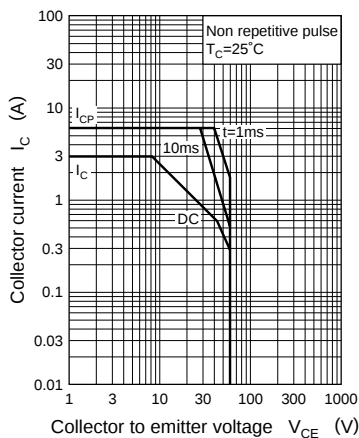
Rank	Q	P
h_{FE}	500 to 1000	800 to 1500



Note: Ordering can be made by the common rank (PQ rank $h_{FE} = 500$ to 1500) in the rank classification.

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$ 

Area of safe operation (ASO)

 $R_{th(t)} - t$ 